



Contents lists available at ScienceDirect

Journal of Alloys and Compounds

journal homepage: www.elsevier.com/locate/jallcom



Synthesis and characterization of zinc oxide nanorods on silicon for the fabrication of *p*-Si/*n*-ZnO heterojunction diode

R.I. Badran^{a,b,*}, Ahmad Umar^{c,d}, S. Al-Heniti^a, A. Al-Hajry^{d,e}, T. Al-Harbi^a

^a Department of Physics, Faculty of Science, King Abdulaziz University, P.O. Box 80203, Jeddah, Saudi Arabia

^b Physics Department, The Hashemite University, P.O. Box 150459, Zarqa, Jordan

^c Department of Chemistry, Faculty of Science, Advanced Materials and Nano-Engineering Laboratory (AMNEL), Najran University, P.O. Box 1988, Najran 11001, Saudi Arabia

^d Centre for Advanced Materials and Nano-Engineering (CAMNE), Najran University, P.O. Box 1988, Najran 11001, Saudi Arabia

^e Department of Physics, Faculty of Science, Najran University, P.O. Box 1988, Najran 11001, Saudi Arabia

ARTICLE INFO

Article history:

Received 4 June 2010

Received in revised form 30 July 2010

Accepted 4 August 2010

Available online 19 August 2010

Keywords:

ZnO

Nanorods

Photoluminescence

Heterojunction diodes

ABSTRACT

Hexagonal-shaped ZnO nanorods were successfully grown on *p*-silicon substrate via thermal evaporation of metallic zinc powder in the presence of oxygen. The grown nanorods were characterized in terms of their structural and optical properties by using X-ray diffraction, FESEM, HRTEM and room-temperature photoluminescence (PL) spectroscopy. It is confirmed from the observed structural and optical properties, that the grown nanorods are well-crystalline with the wurtzite hexagonal phase and are preferentially grown along the [000 1] direction and exhibiting good optical properties. The as-grown *n*-ZnO nanorods on *p*-silicon (*n*-ZnO/*p*-Si) substrate were used to fabricate *p*-*n* heterojunction diode which attains a turn-on voltage of ~0.5 V. Temperature-dependant (298, 323, 343, 363, 383, and 423 K) *I*-*V* characteristics for the fabricated diode were also examined and demonstrated in this paper. It was found that the fabricated heterojunction diode was reasonably stable at higher temperatures and the series resistance slightly increases with increasing the temperature.